

3DD8, 3DD9**NPN Silicon Low Frequency High Power Transistor****Features:**

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications								
			3DD8					3DD9			
			A	B	C	D	E	F	G	H	I
Collector-Emitter Voltage	V_{CEO}	V	50	100	150	200	250	300	400	500	600
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	50	100	150	200	250	300	400	500	600
Emitter-Base Voltage	V_{EBO}	V	5					5			
Max. Collector Current	I_{CM}	A	A~F \leq 10, G~I \leq 5					A~F \leq 15, G~I \leq 7.5			
Max. Collector Dissipation	P_{CM}	W	100 (Tc \leq 75°C)					150 (Tc \leq 75°C)			
Junction Temperature	T_{jm}	°C	175								
Storage Temperature	T_{stg}	°C	-55~+175								
Collector-Emitter Leakage Current	I_{CEO}	mA	5.0 (A: $V_{CE}=30V$;B: $V_{CE}=50V$; C~I: $V_{CE}=100V$)								
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.5(A~F: $I_C=5.0A, I_B=0.5A$) 2.0 (G~I: $I_C=2.5A, I_B=0.5A$)					1.5(A~F: $I_C=7.5A, I_B=0.75A$) 2.0 (G~I: $I_C=4.0A, I_B=0.8A$)			
DC Current Gain	h_{FE}		Max.:120 Min.:15(A~F: $V_{CE}=5V, I_C=5.0A$) Min.: 7 (G~I: $V_{CE}=10V, I_C=2.5A$)					Max.:120 Min.:15 (A~F: $V_{CE}=5V, I_C=7.5A$) Min.: 7 (G~I: $V_{CE}=10V, I_C=5.0A$)			
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	≥ 5 ($I_E=5mA$)					≥ 5 ($I_E=10mA$)			

hFE Colored:

Color	Brown	Red	Orange	Yellow	Green	Blue
h_{FE}	7~15	15~25	25~40	40~55	55~80	80~120

Outline and Dimensions: